VHF/UHF Transistors NPN Silicon

COLLECTOR 3 BASE 2 EMITTER

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	25	Vdc
Collector-Base Voltage	Vсво	30	Vdc
Emitter-Base Voltage	V _{EBO}	3.0	Vdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.0 8.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V(BR)CEO	25	_	Vdc	
Collector-Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)		30	_	Vdc	
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V(BR)EBO	3.0	_	Vdc	
Collector Cutoff Current $(V_{CB} = 25 \text{ Vdc}, I_E = 0)$	ICBO	_	100	nAdc	
Emitter Cutoff Current (V _{EB} = 2.0 Vdc, I _C = 0)	IEBO	_	100	nAdc	

MPSH10 MPSH11

Motorola Preferred Devices

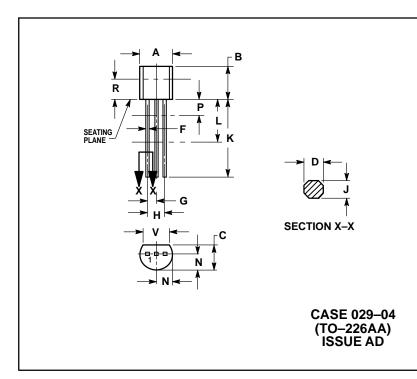


MPSH10 MPSH11

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic			Min	Max	Unit
ON CHARACTERISTICS		•		•	•
DC Current Gain (I _C = 4.0 mAdc, V _{CE} = 10 Vdc)		hFE	60	_	_
Collector – Emitter Saturation Voltage (I _C = 4.0 mAdc, I _B = 0.4 mAdc)		VCE(sat)	_	0.5	Vdc
Base-Emitter On Voltage (I _C = 4.0 mAdc, V _{CE} = 10 Vdc)		V _{BE} (on)	_	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS					•
Current-Gain — Bandwidth Product (I _C = 4.0 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)		fΤ	650	_	MHz
Collector–Base Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{cb}	_	0.7	pF
Common–Base Feedback Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	MPSH10 MPSH11	C _{rb}	0.35 0.6	0.65 0.9	pF
Collector Base Time Constant (I _C = 4.0 mAdc, V _{CB} = 10 Vdc, f = 31.8 MHz)		rb'C _C	_	9.0	ps

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3 43	

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR